



SSC8L32GN4

N-Channel Enhancement Mode MOSFET

➤ Features

VDS	VGS	RDSON Typ.	ID
30V	±20V	2.6mR@10V	80A
		3.6mR@4V5	

➤ Description

This device uses advanced trench technology to provide excellent RDSON and low gate charge. This device is suitable for use as a load switch or in PWM applications.

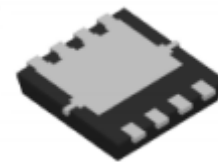
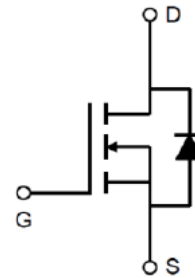
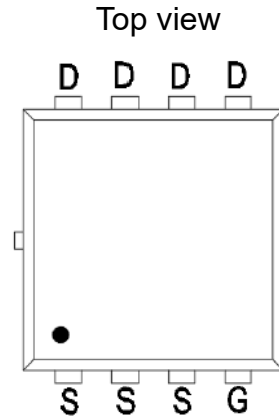
➤ Applications

- Load Switch
- Portable Devices
- DCDC conversion

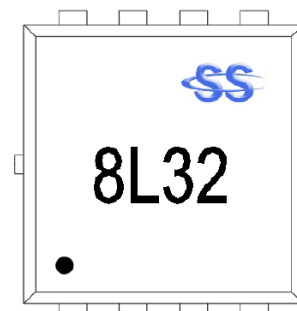
➤ Ordering Information

Device	Package	Shipping
SSC8L32GN4	PDFN3.3X3.3	5000/Reel

➤ Pin configuration



Bottom View



Marking

**➤ Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V_{DSS}	Drain-to-Source Voltage	30	V	
V_{GSS}	Gate-to-Source Voltage	± 20	V	
I_D	Continuous Drain Current ^d	$T_C=25^{\circ}\text{C}$	80	A
		$T_C=100^{\circ}\text{C}$	72	
I_{DSM}	Continuous Drain Current ^a	$T_A=25^{\circ}\text{C}$	66	A
		$T_A=70^{\circ}\text{C}$	59	
I_{DM}	Pulsed Drain Current ^b	120	A	
P_D	Power Dissipation ^c	$T_C=25^{\circ}\text{C}$	60	W
		$T_C=100^{\circ}\text{C}$	28	
P_{DSM}	Power Dissipation ^a	$T_A=25^{\circ}\text{C}$	4.25	W
		$T_A=70^{\circ}\text{C}$	3.4	
I_{AS}	Avalanche Current ^b	125	A	
E_{AS}	Avalanche Energy ^b L=0.05mH	45	mJ	
T_J	Operation junction temperature	-55~150	$^{\circ}\text{C}$	
T_{STG}	Storage temperature range	-55~150		
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	70	$^{\circ}\text{C/W}$	
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	10		

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with $T_A=25^{\circ}\text{C}$.The value in any given application depends on the user is specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is packed limited.

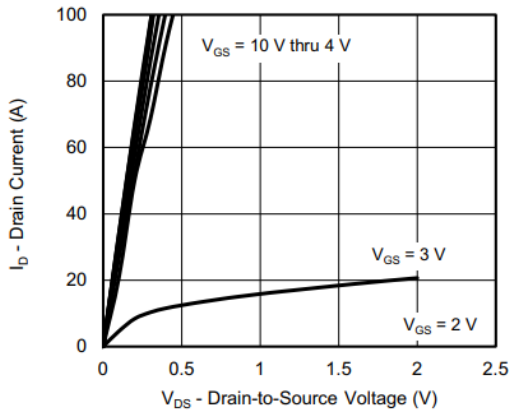


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

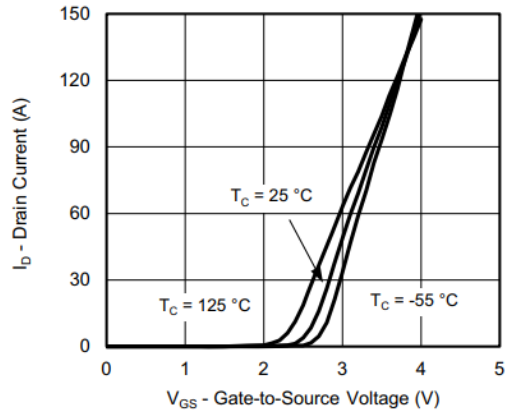
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250uA	30			V
VGS (th)	Gate Threshold Voltage	VDS=VGS, ID=250uA	1	1.5	2.2	V
RDS(on)	Drain-Source On- Resistance	VGS=10V, ID=20A		2.6	3.8	mR
		VGS=4.5V, ID=10A		3.6	5	
IDSS	Zero Gate Voltage Drain Current	VDS=30V, VGS=0V			1	uA
IGSS	Gate-Source leak current	VGS=±20V, VDS=0V			±100	nA
VSD	Forward Voltage	VGS=0V, IS=1A			1.1	V
Ciss	Input Capacitance	VDS=20V, VGS=0V, f=1MHZ		2560		pF
Coss	Output Capacitance			560		
Crss	Reverse Transfer Capacitance			130		
Qg	Total Gate Charge	VDS=15V , ID=20A , VGS=4.5V		29		nC
Qgs	Gate to source charge			6		
Qgd	Gate to drain charge			5		
TD(ON)	Turn-on delay time	VGEN=10V, VDS=15V, RL=15R, RG=3R, ID=1A		15		ns
Tr	Rise time			5		
TD(OFF)	Turn-off delay time			35		
Tf	Fall time			10		



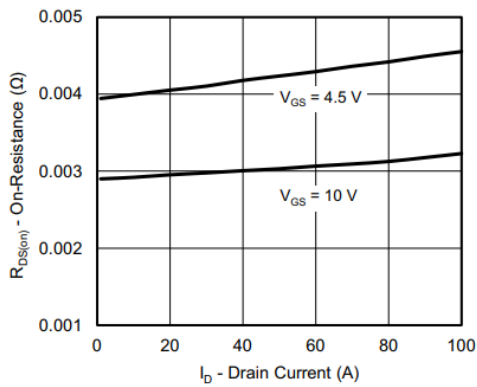
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



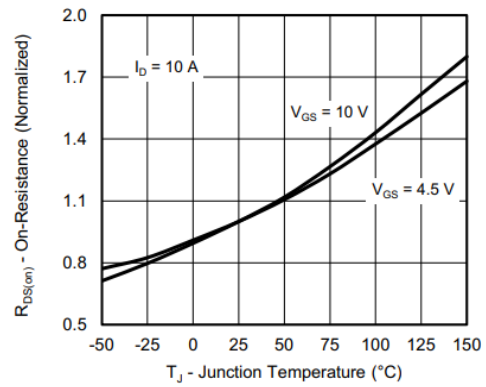
Output Characteristics



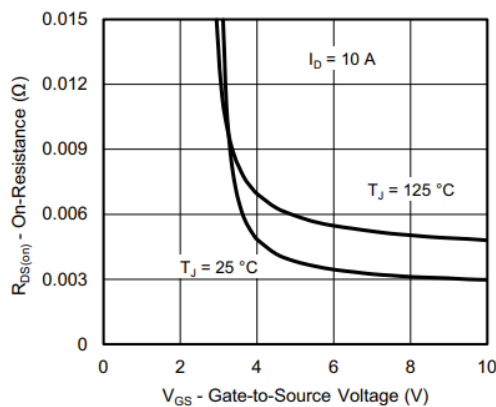
Transfer Characteristics



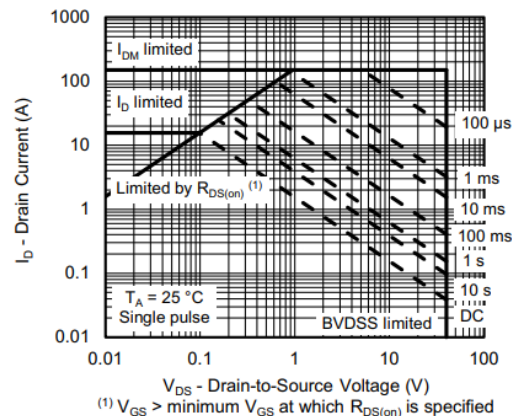
On-Resistance vs. Drain Current and Gate Voltage



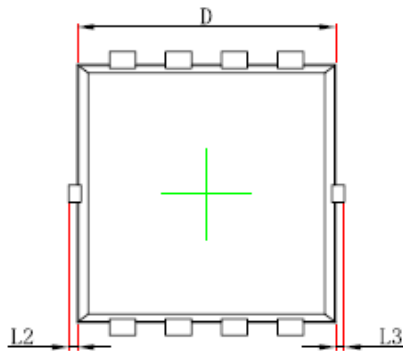
On-Resistance vs. Junction Temperature



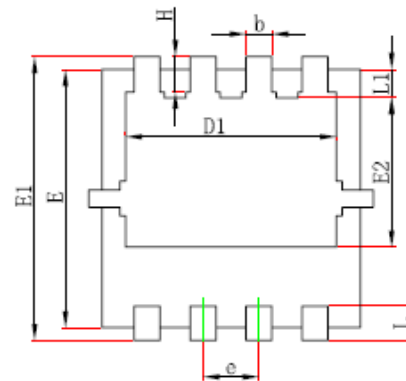
On-Resistance vs. Gate-to-Source Voltage



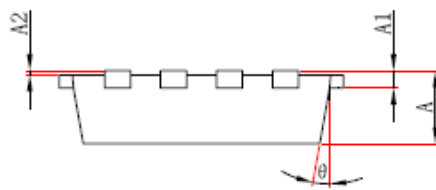
Safe Operating Area, Junction-to-Ambient

➤ Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Package: PDNF3.3X3.3-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°



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